

Journal of Nanophotonics

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[DOI: [10.1117/1.JNP.6.060103](https://doi.org/10.1117/1.JNP.6.060103)]

This article was originally published in Vol. 6 of the *Journal of Nanophotonics* on 24 February 2012 in the wrong section of the table of contents and with an incorrect citation identifier (CID) of 013502. The paper was removed and republished online with the correct CID of 063502 on 8 March 2012. This change was made in order for the paper to appear under the correct section heading, "Research Papers."

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